

COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

Device	V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
Q1 N-Channel	30V	460mΩ @ V _{GS} = 4.5V	1.1A
		560mΩ @ V _{GS} = 2.5V	0.9A
Q2 P-Channel	-30V	1000mΩ @ V _{GS} = -4.5V	-0.7A
		1500mΩ @ V _{GS} = -2.5V	-0.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

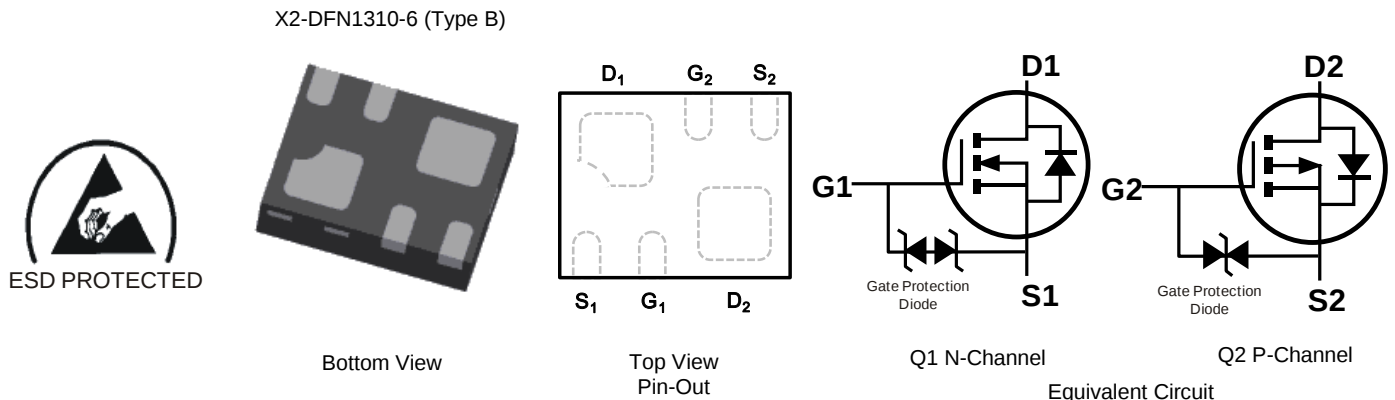
- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Footprint of just 1.3 mm²
- Ultra Low Profile Package – 0.35mm Profile
- Low Gate Threshold Voltage
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: X2-DFN1310-6 (Type B)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E4)
- Weight: 0.002 grams (Approximate)

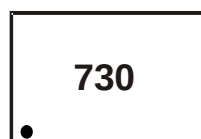


Ordering Information (Note 4)

Part Number	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMC3730UFL3-7	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



730 = Product Type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1	Q2	Unit
Drain-Source Voltage			V _{DSS}	30	-30	V
Gate-Source Voltage			V _{GSS}	±8	±8	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	1.1	-0.7	A
		T _A = +70°C		0.8	-0.6	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.39	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	330	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	0.81	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	156	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	51	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (N-Channel Q1) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.45	0.72	0.95	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	291	460	mΩ	V _{GS} = 4.5V, I _D = 200mA
			335	560		V _{GS} = 2.5V, I _D = 100mA
			398	730		V _{GS} = 1.8V, I _D = 75mA
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	65.9	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	5.8	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	4.3	—	pF	
Gate Resistance	R _G	—	64	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _G	—	0.9	—	nC	
Gate-Source Charge	Q _{GS}	—	0.1	—	nC	
Gate-Drain Charge	Q _{GD}	—	0.1	—	nC	V _{DS} = 15V, V _{GS} = 4.5V, I _D = 1A
Turn-On Delay Time	t _{D(ON)}	—	3.6	—	ns	
Turn-On Rise Time	t _R	—	6.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	19.4	—	ns	V _{GS} = 4.5V, V _{DS} = 10V, R _G = 6Ω, I _D = 1A
Turn-Off Fall Time	t _F	—	6.9	—	ns	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

Electrical Characteristics (P-Channel Q2) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	-0.78	-1.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	644	1,000	mΩ	V _{GS} = -4.5V, I _D = -400mA
			769	1,500		V _{GS} = -2.5V, I _D = -200mA
			949	2,000		V _{GS} = -1.8V, I _D = -100mA
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	83	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	6.2	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	4.1	—	pF	
Gate Resistance	R _G	—	177	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _G	—	0.9	—	nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -1A
Gate-Source Charge	Q _{GS}	—	0.1	—	nC	
Gate-Drain Charge	Q _{GD}	—	0.2	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.0	—	ns	V _{GS} = -4.5V, V _{DS} = -10V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _R	—	11.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	28.9	—	ns	
Turn-Off Fall Time	t _F	—	15.5	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

Typical Characteristics (N-Channel)

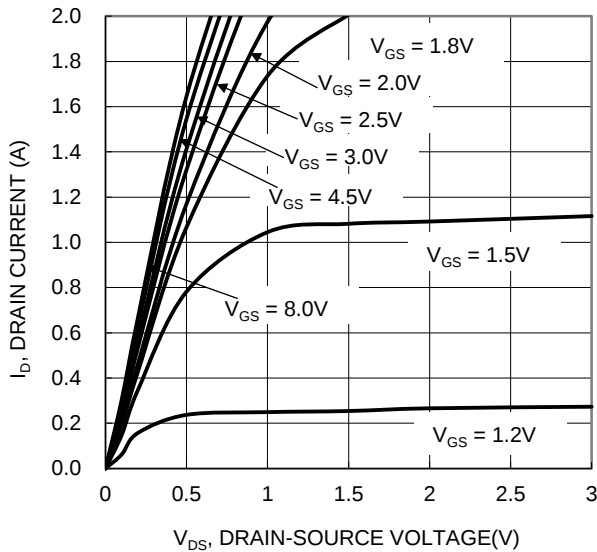


Figure 1. Typical Output Characteristic

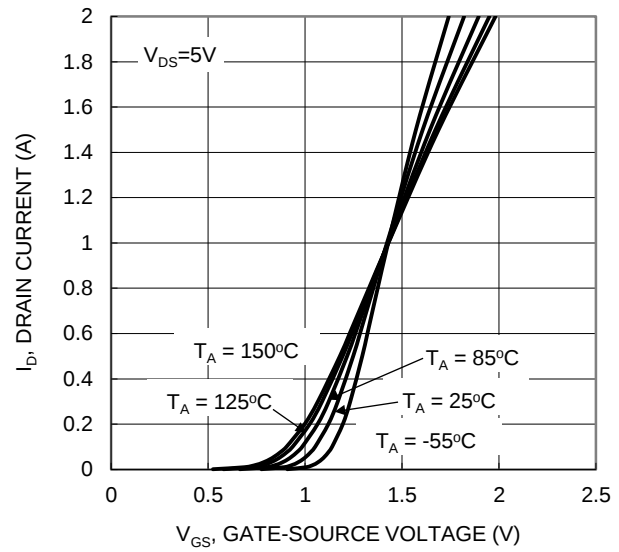


Figure 2. Typical Transfer Characteristic

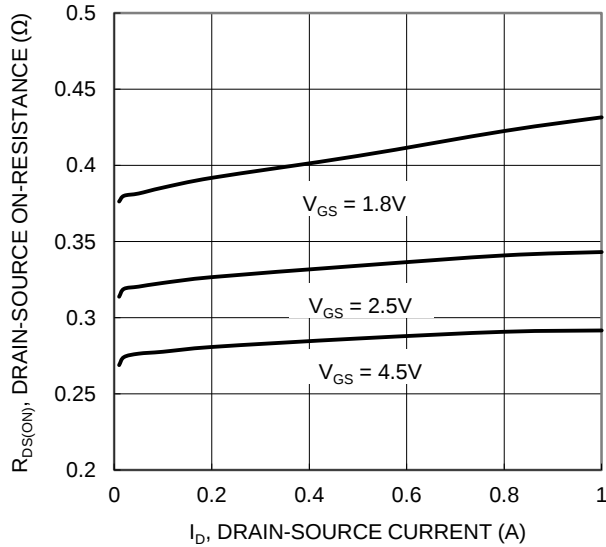


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

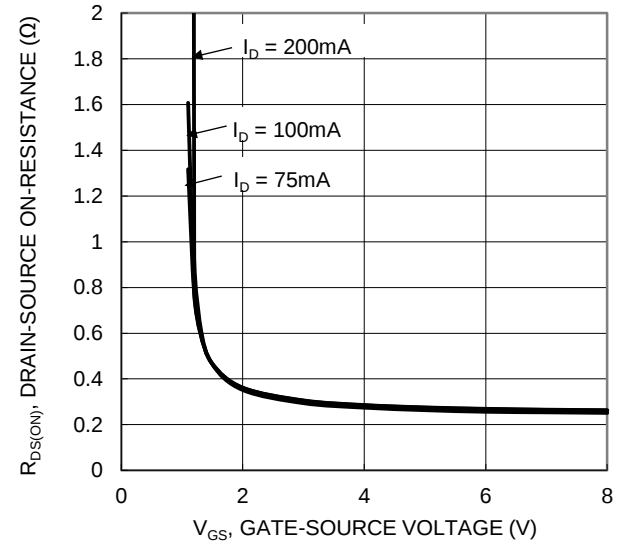


Figure 4. Typical Transfer Characteristic

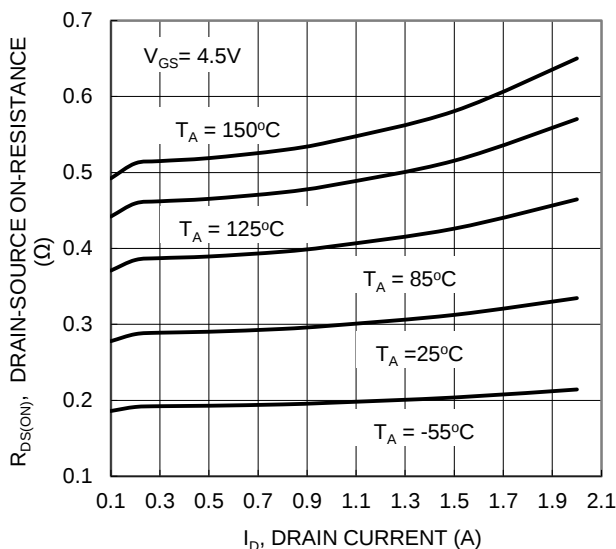


Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature

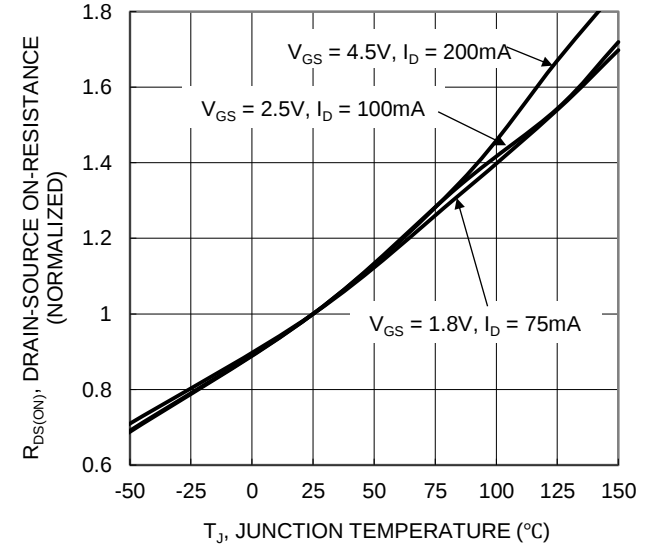


Figure 6. On-Resistance Variation with Junction Temperature

Typical Characteristics (N-Channel) (Continued)

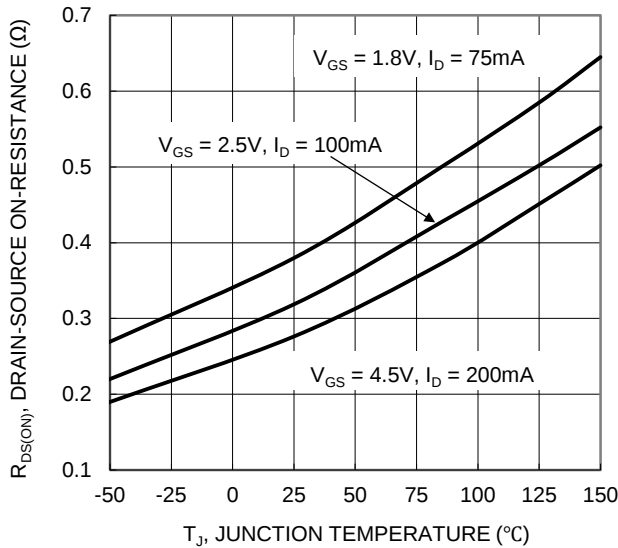


Figure 7. On-Resistance Variation with Junction Temperature

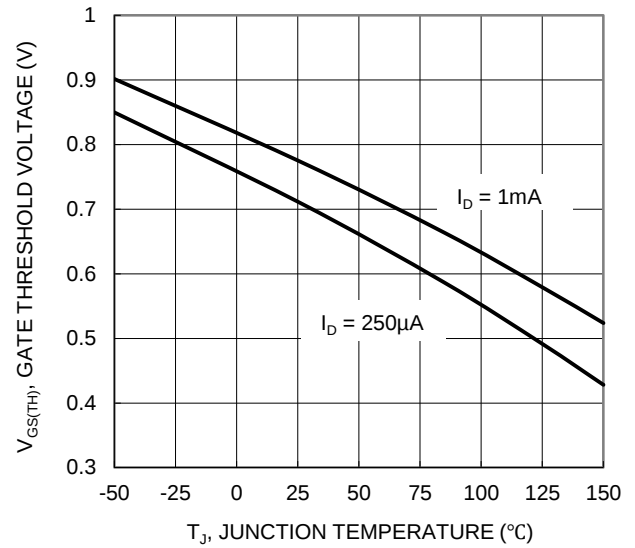


Figure 8. Gate Threshold Variation vs Junction Temperature

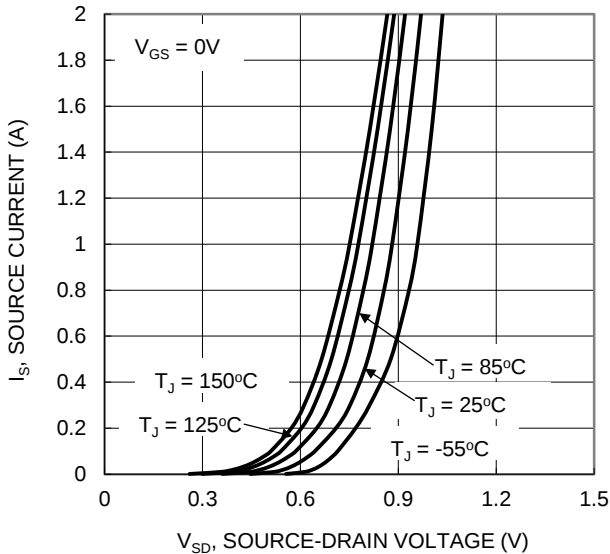


Figure 9. Diode Forward Voltage vs. Current

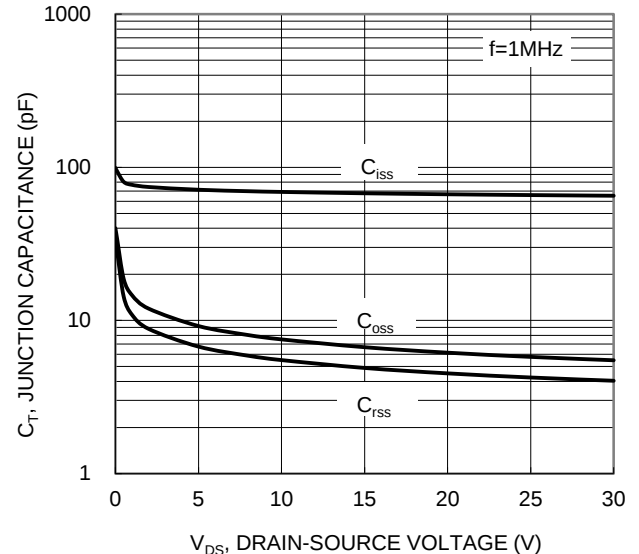


Figure 10. Typical Junction Capacitance

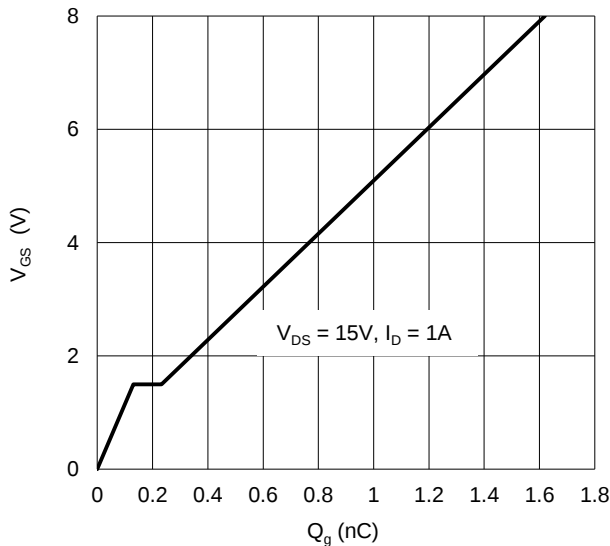


Figure 11. Gate Charge

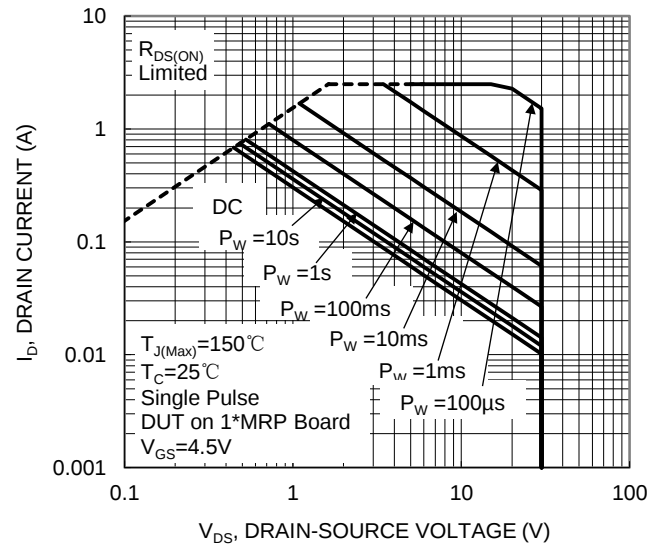


Figure 12. SOA, Safe Operation Area

Typical Characteristics (P-Channel)

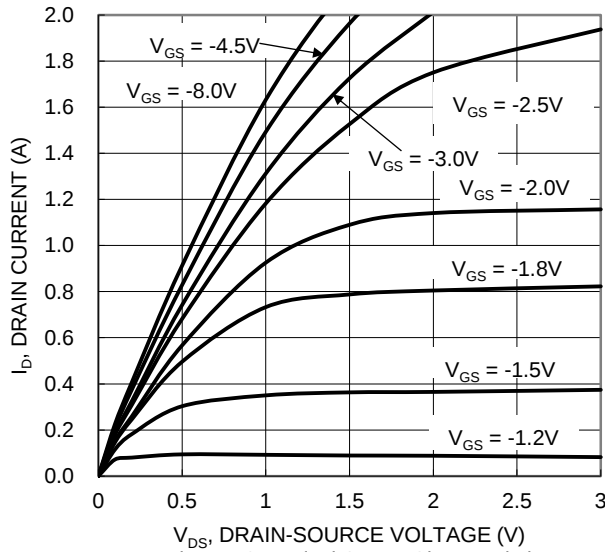


Figure 13. Typical Output Characteristic

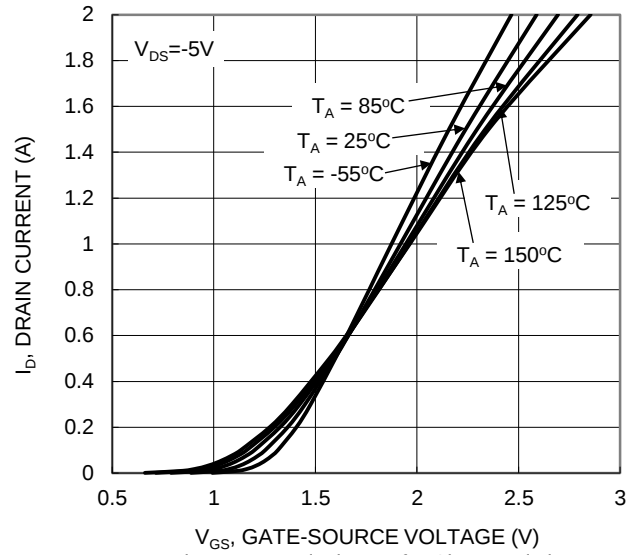


Figure 14. Typical Transfer Characteristic

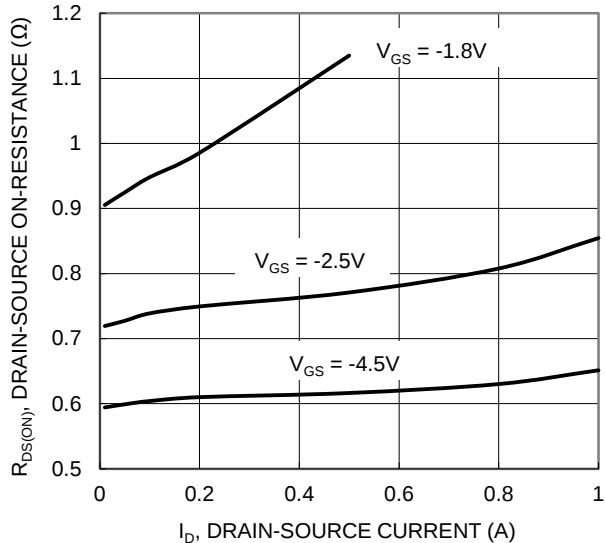


Figure 15. Typical On-Resistance vs Drain Current and Gate Voltage

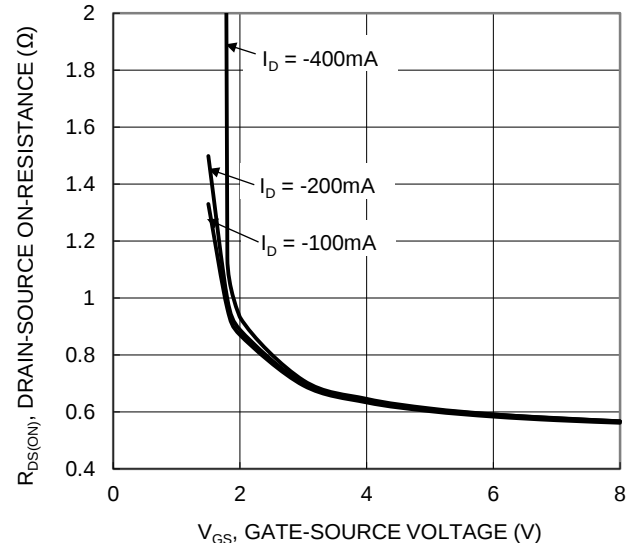


Figure 16. Typical Transfer Characteristic

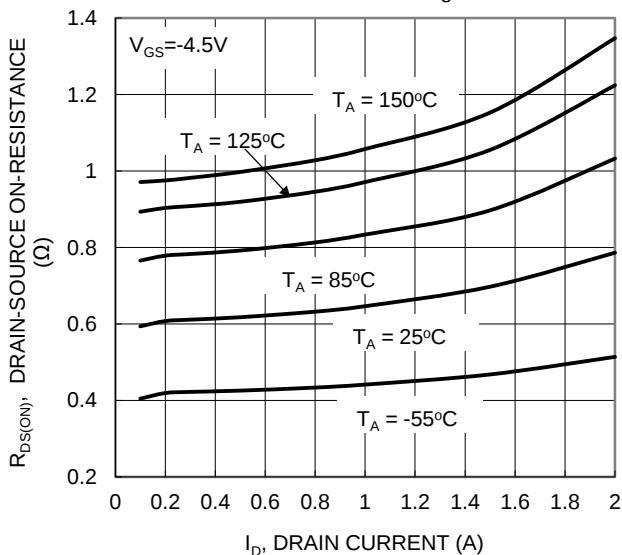


Figure 17. Typical On-Resistance vs Drain Current and Junction Temperature

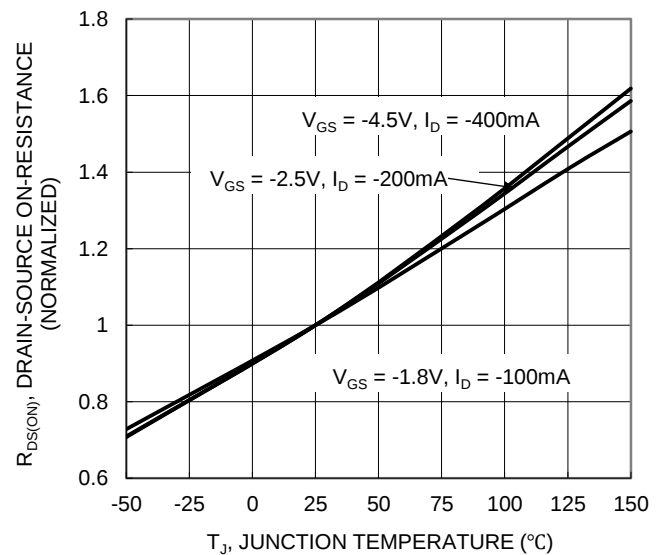


Figure 18. On-Resistance Variation with Junction Temperature

Typical Characteristics (P-Channel) (Continued)

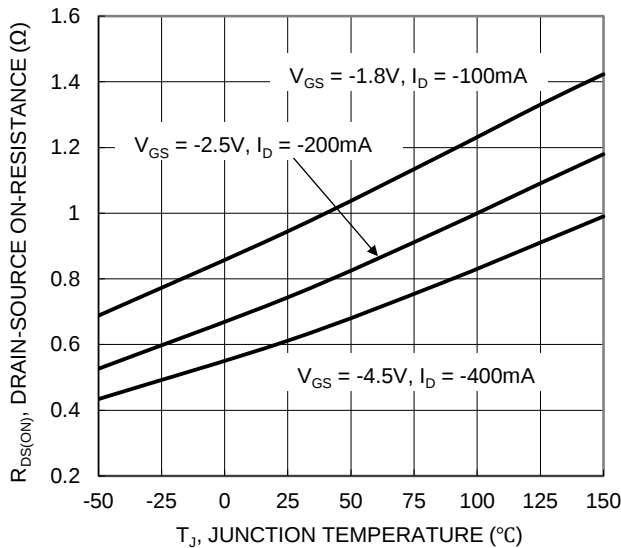


Figure 19. On-Resistance Variation with Junction Temperature

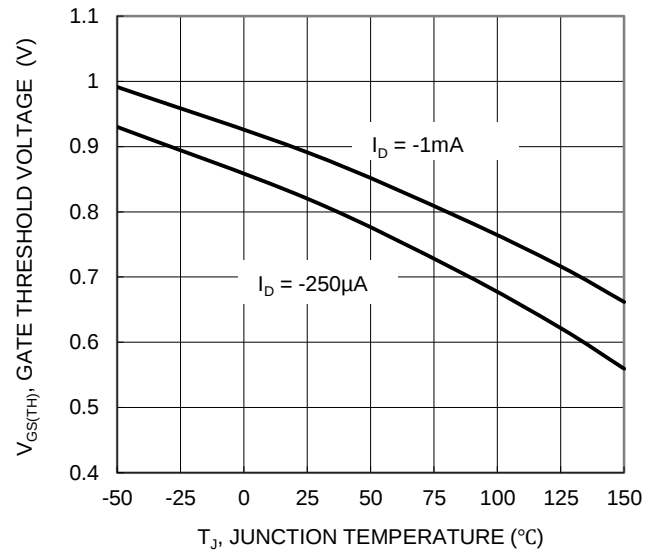


Figure 20. Gate Threshold Variation vs Junction Temperature

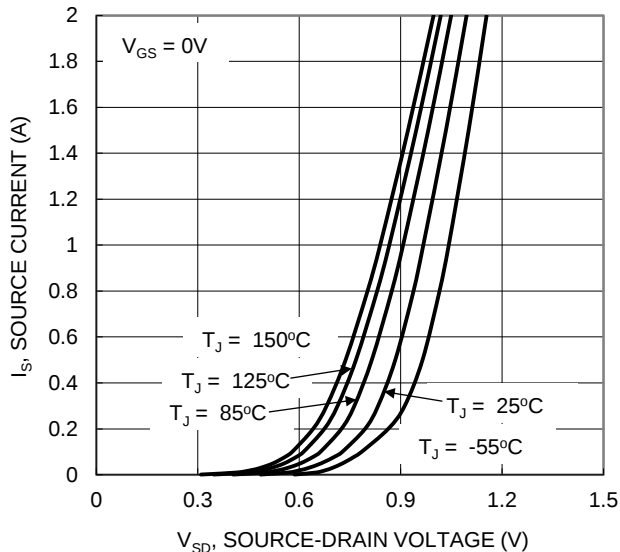


Figure 21. Diode Forward Voltage vs. Current

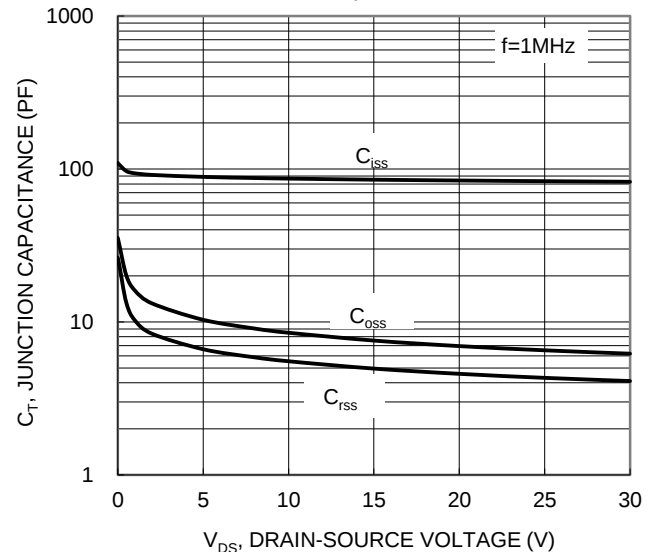


Figure 22. Typical Junction Capacitance

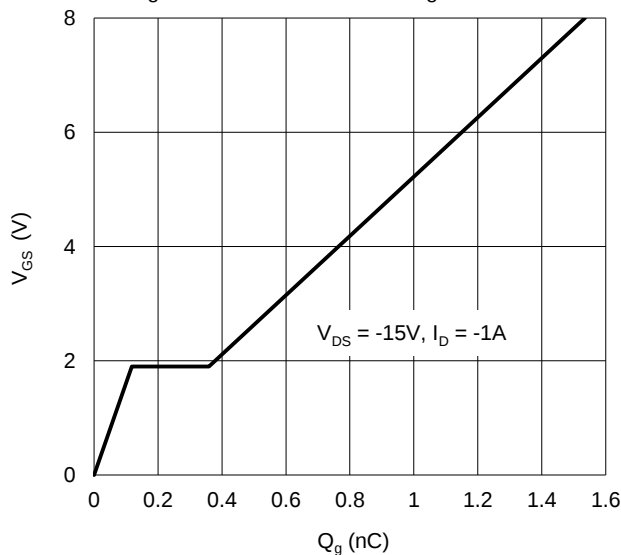


Figure 23. Gate Charge

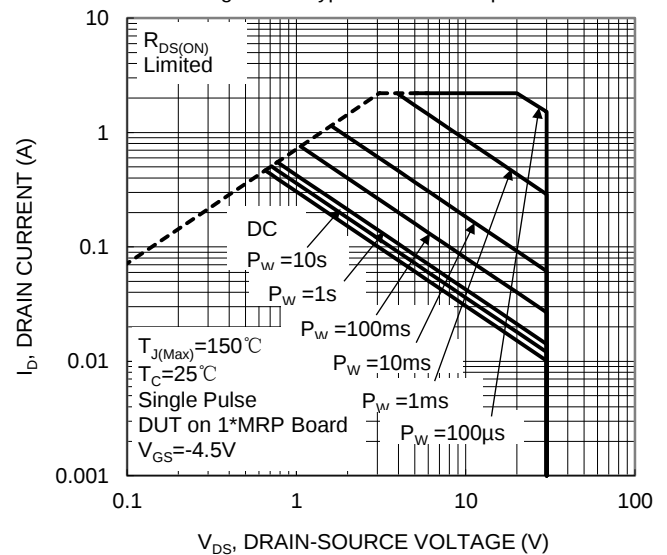


Figure 24. SOA, Safe Operation Area

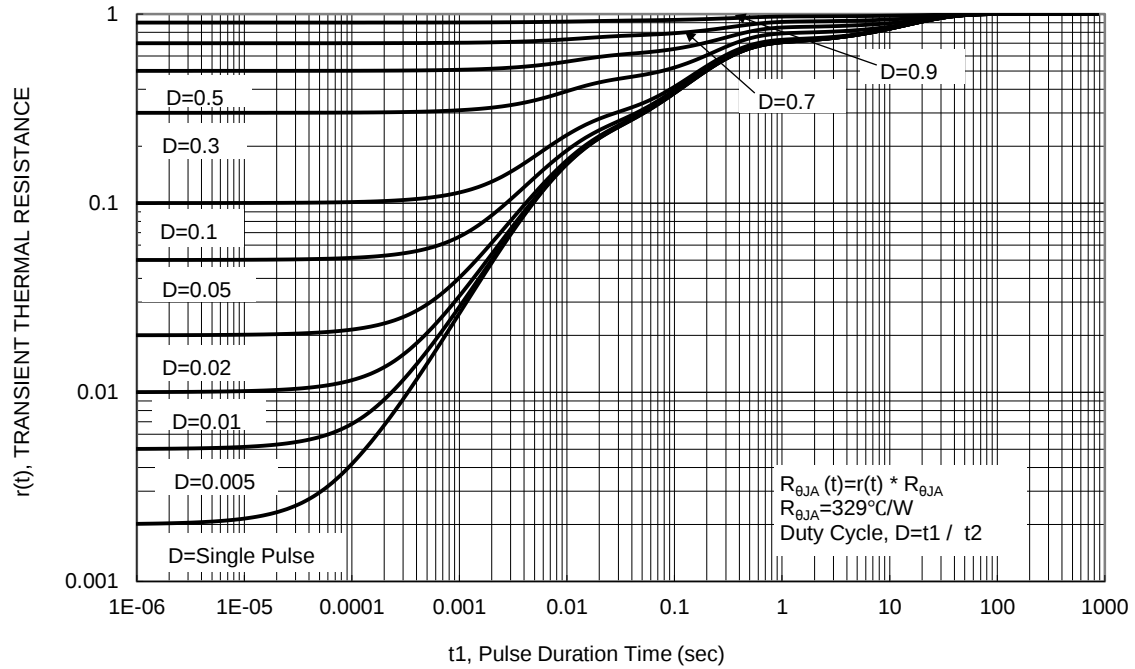
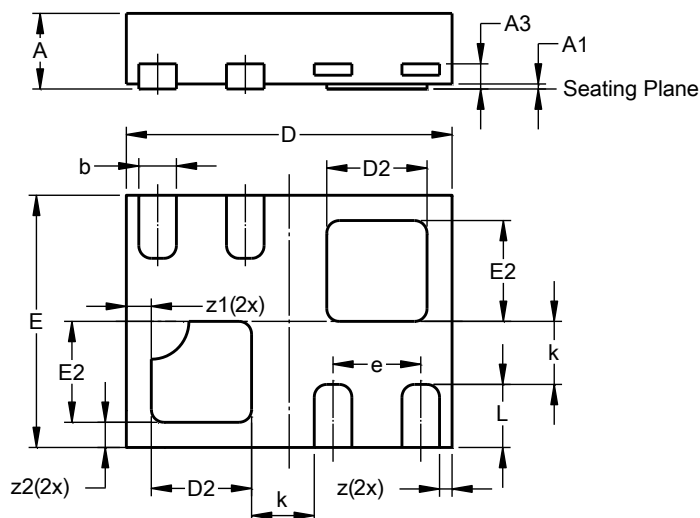


Figure 25. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1310-6 (Type B)

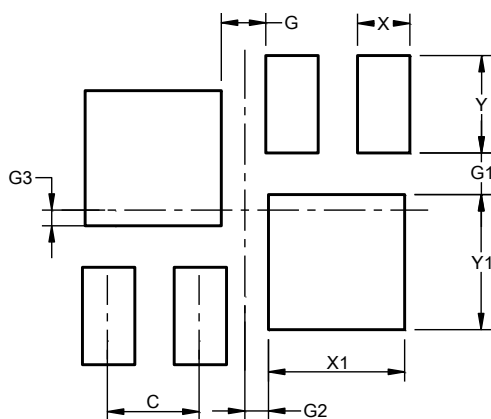


X2-DFN1310-6 (Type B)			
Dim	Min	Max	Typ
A	0.25	0.35	0.30
A1	0	0.05	0.02
A3	—	—	0.100
b	0.10	0.20	0.15
D	1.25	1.35	1.30
D2	0.30	0.50	0.40
E	0.95	1.05	1.00
E2	0.30	0.50	0.40
e	—	—	0.35
k	0.15	—	—
L	0.20	0.30	0.25
z	—	—	0.05
z1	—	—	0.10
z2	—	—	0.10
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1310-6 (Type B)



Dimensions	Value (in mm)
C	0.350
G	0.17
G1	0.16
G2	0.09
G3	0.06
X	0.20
X1	0.52
Y	0.375
Y1	0.52

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated

www.diodes.com



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331